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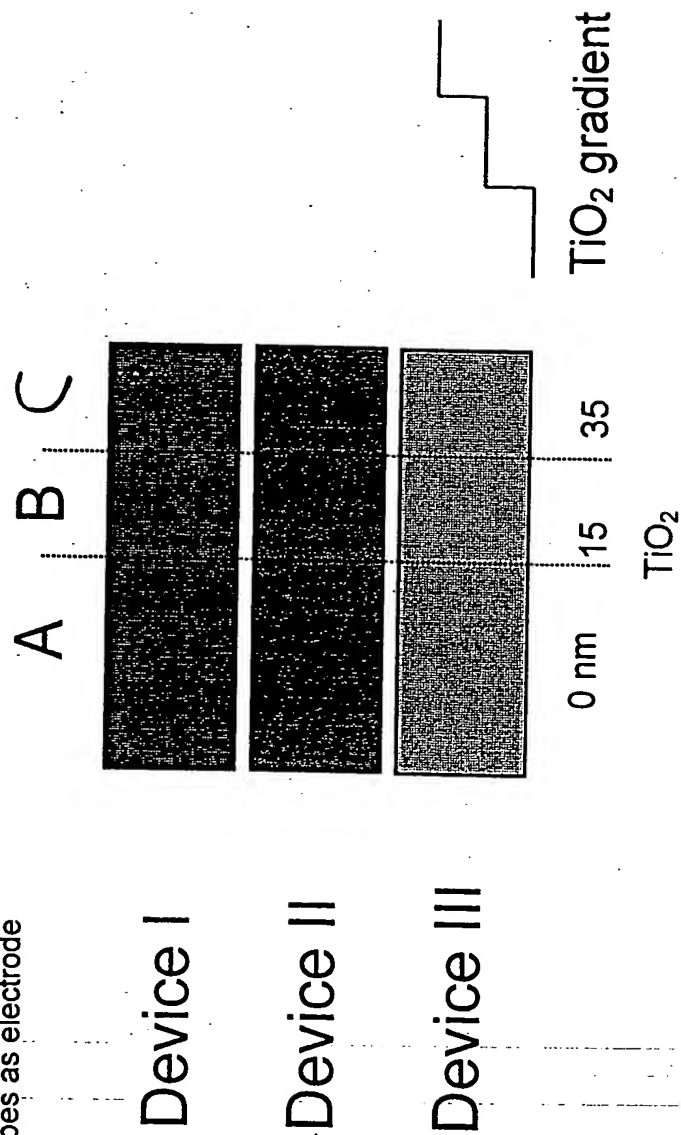
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- Step 1: CuPc 35 nm on 3 substrates
- Step 2: ST1/1 and ST2 on two of the substrates
- Step 3: TiO₂ thickness gradient (0, 15, 35 nm)
- Step 4: 24 Al stripes as electrode

Figure 1



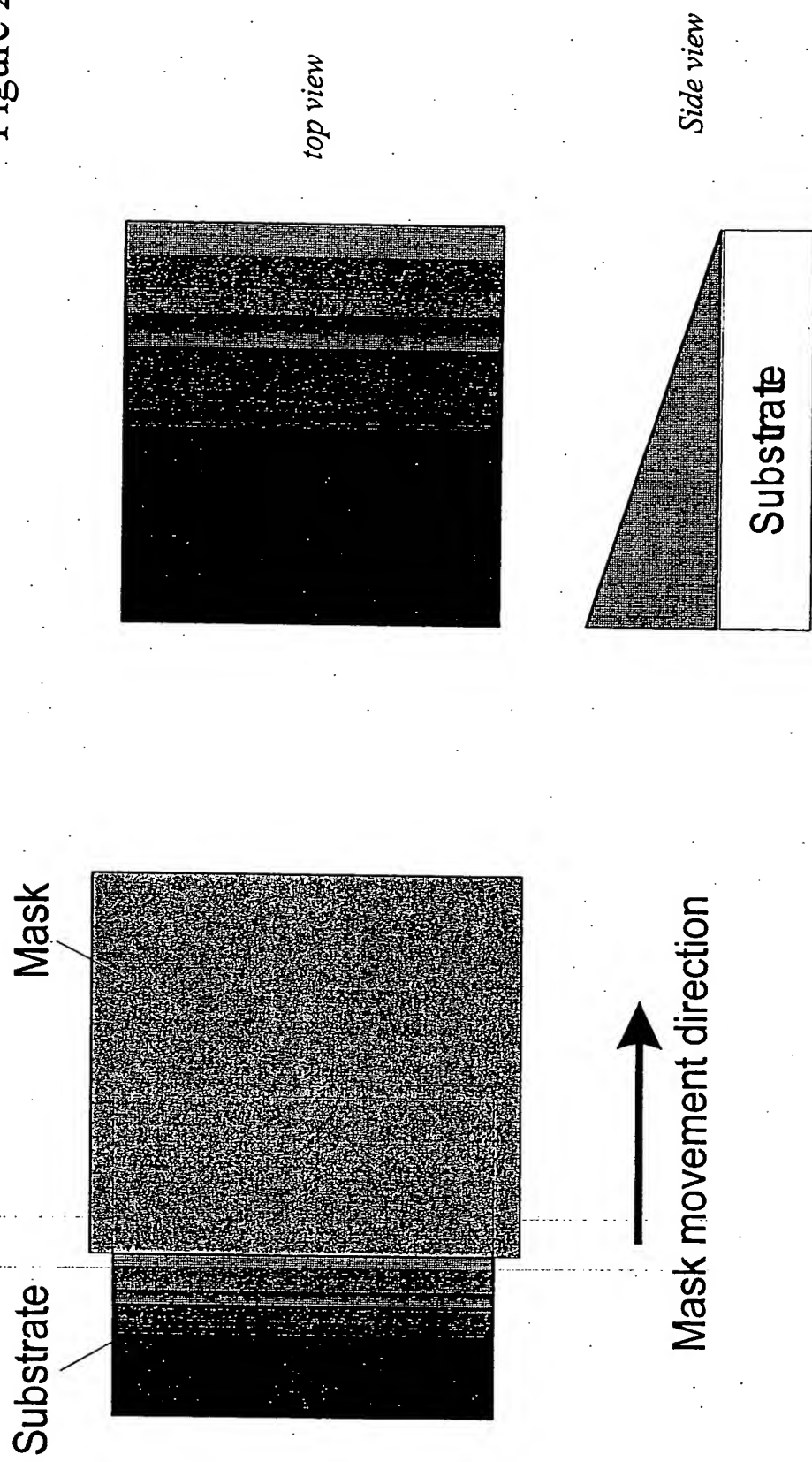
Device structure

Device I: ITO/CuPc (35 nm)/ST1_1 (25 nm)/TiO₂ (gradient)/Al

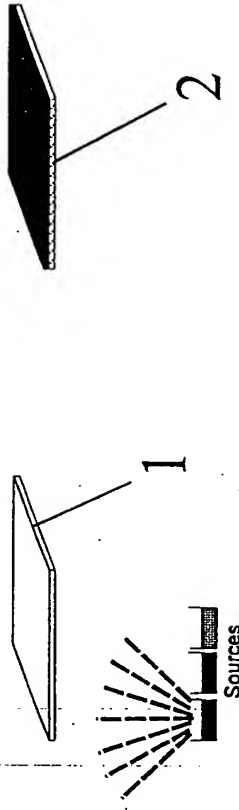
Device II: ITO/CuPc (35 nm)/ST 2 (25 nm)/TiO₂ (gradient)/Al

Device III: ITO/CuPc (35 nm)/TiO₂ (gradient)/Al

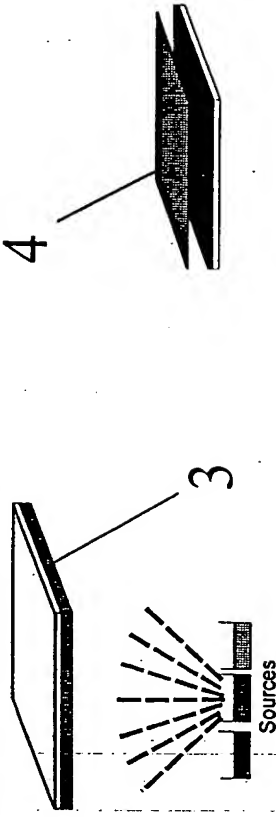
Figure 2



1. Step: constant thickness layer of HTM



2. Step: constant thickness of ST1 or ST2



3. Step: step gradient of TiO_2

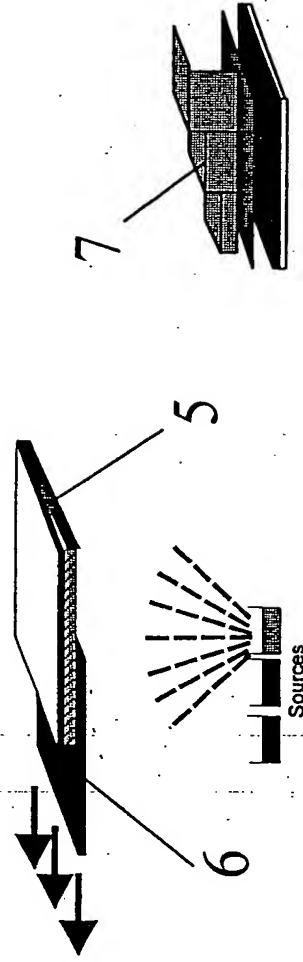


Figure 3

SEM of cell cross section

Figure 4

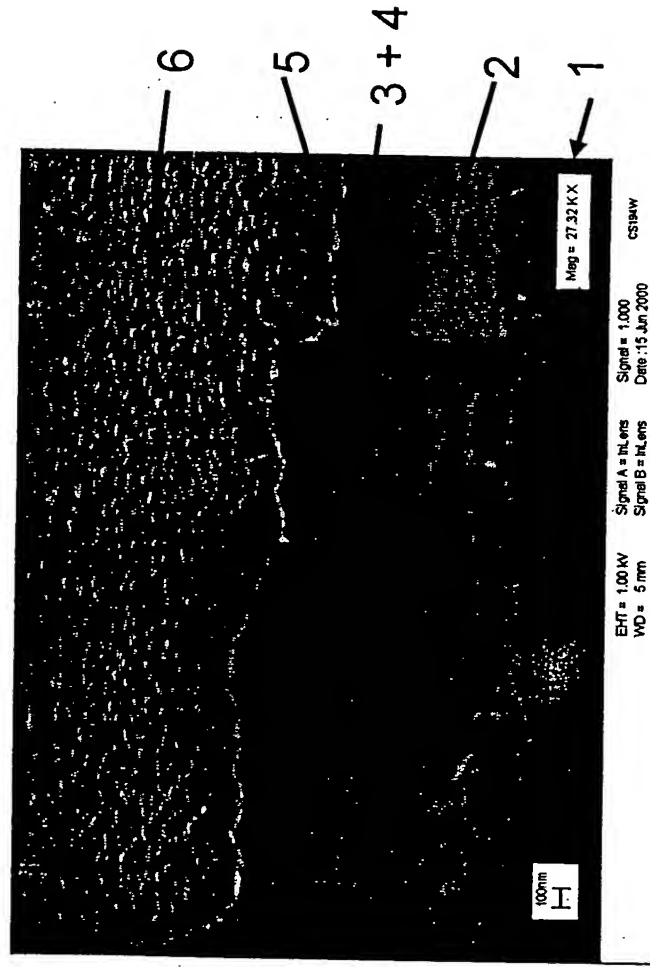


Figure 5

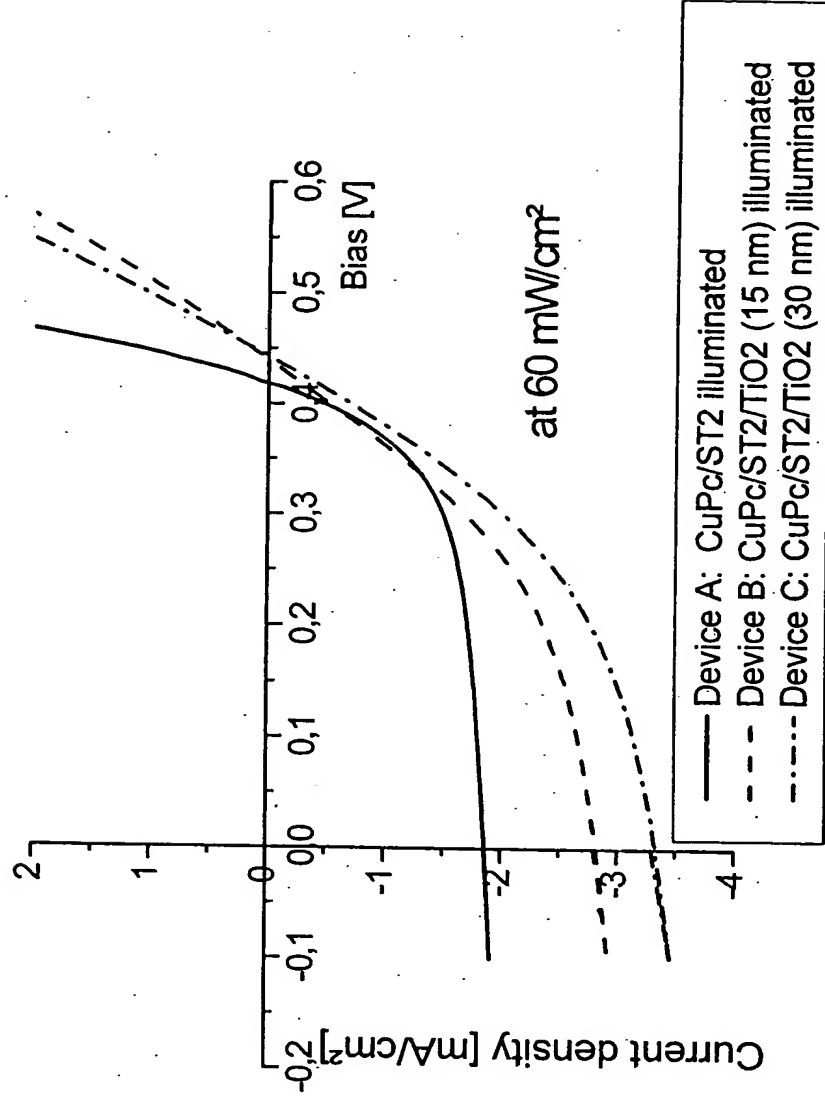


Figure 6

Device C

